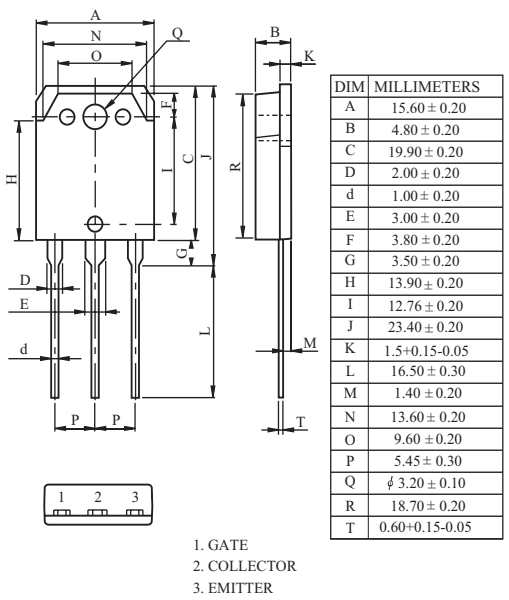
General Description

KEC Field Stop IGBTs offer low switching losses, high energy efficiency and high avalanche ruggedness for soft switching application such asIH(induction heating), microwave oven, etc.



DIM	MILLIMETERS
A	15.60 ± 0.20
B	4.80 ± 0.20
C	19.90 ± 0.20
D	2.00 ± 0.20
d	1.00 ± 0.20
E	3.00 ± 0.20
F	3.80 ± 0.20
G	3.50 ± 0.20
H	13.90 ± 0.20
I	12.76 ± 0.20
J	23.40 ± 0.20
K	1.5+0.15-0.05
L	16.50 ± 0.30
M	1.40 ± 0.20
N	13.60 ± 0.20
O	9.60 ± 0.20
P	5.45 ± 0.30
Q	ϕ 3.20 ± 0.10
R	18.70 ± 0.20
T	0.60+0.15-0.05

TO-3P(N)-E

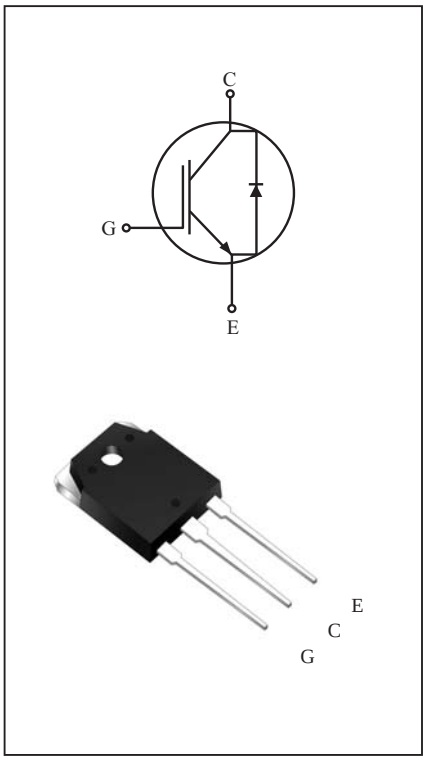
FEATURES

- High speed switching
- High system efficiency
- Soft current turn-off waveforms
- Extremely enhanced avalanche capability

MAXIMUM RATING (Ta=25℃)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Emitter Voltage		V_{CES}	1350	V
Gate-Emitter Voltage		V_{GES}	±20	V
Collector Current	@T_C=25℃	I_C	30	A
	@T_C=100℃		15	A
Pulsed Collector Current		I_{CM}*	45	A
Diode Continuous Forward Current	@T_C=100℃	I_F	15	A
Diode Maximum Forward Current		I_{FM}	45	A
Maximum Power Dissipation	@T_C=25℃	P_D	150	W
	@T_C=100℃		60	W
Maximum Junction Temperature		T_j	150	℃
Storage Temperature Range		T_{stg}	-55 to + 150	℃

*Repetitive rating : Pulse width limited by max. junction temperature



THERMAL CHARACTERISTIC

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Junction to Case (IGBT)	R_{thJC}	0.82	℃/W
Thermal Resistance, Junction to Case (DIODE)	R_{thJC}	2.3	℃/W
Thermal Resistance, Junction to Ambient	R_{thJA}	40	℃/W

ELECTRICAL CHARACTERISTICS (Ta=25℃)

CHARACTERISTIC	SYMBOL	TEST CONDITION		MIN.	TYP.	MAX.	UNIT
Static							
Collector-Emitter Breakdown Voltage	BV_{CES}	V_{GE}=0V , I_C=1.0mA		1350	-	-	V
Collector Cut-off Current	I_{CES}	V_{GE}=0V, V_{CE}=1350V		-	-	1.0	mA
Gate Leakage Current	I_{GES}	V_{CE}=0V, V_{GE}=±20V		-	-	±100	nA
Gate Threshold Voltage	$V_{GE(th)}$	V_{GE}=V_{CE}, I_C=15mA		5.1	6.4	7.7	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	V_{GE}=15V, I_C=15A		-	1.76	2.11	V
		V_{GE}=15V, I_C=15A, T_C = 125℃		-	1.97	-	V
		V_{GE}=15V, I_C=30A		-	2.18	-	V
Diode Forward Voltage	V_F	I_F = 15A	T_C=25℃	-	1.78	2.1	V
			T_C=125℃	-	1.9	-	V
Dynamic							
Total Gate Charge	Q_g	V_{CC}=600V, V_{GE}=15V, I_C= 15A		-	152	182	nC
Gate-Emitter Charge	Q_{ge}			-	23	-	nC
Gate-Collector Charge	Q_{gc}			-	72	-	nC
Turn-On Delay Time	$t_{d(on)}$	V_{CC}=600V, I_C=15A, V_{GE}=15V,R_G=10Ω Inductive Load, T_C = 25℃		-	38	-	ns
Rise Time	t_r			-	14	-	ns
Turn-Off Delay Time	$t_{d(off)}$			-	215	-	ns
Fall Time	t_f			-	120	-	ns
Turn-On Switching Loss	E_{on}			-	267	-	mJ
Turn-Off Switching Loss	E_{off}			-	0.5	-	mJ
Total Switching Loss	E_{ts}			-	3.17	-	mJ
Turn-On Delay Time	$t_{d(on)}$	V_{CC}=600V, I_C=15A, V_{GE}=15V, R_G=10Ω Inductive Load, T_C = 125℃		-	36	-	ns
Rise Time	t_r			-	13	-	ns
Turn-Off Delay Time	$t_{d(off)}$			-	234	-	ns
Fall Time	t_f			-	229	-	ns
Turn-On Switching Loss	E_{on}			-	2.6	-	mJ
Turn-Off Switching Loss	E_{off}			-	1.1	-	mJ
Total Switching Loss	E_{ts}			-	3.7	-	mJ
Input Capacitance	C_{ies}	V_{CE}=30V, V_{GE}=0V, f=1MHz		-	2614	-	pF
Ouput Capacitance	C_{oes}			-	66	-	pF
Reverse Transfer Capacitance	C_{res}			-	44	-	pF

Marking

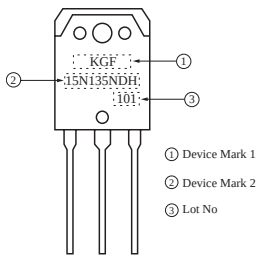


Fig 1. Saturation Voltage Characteristics

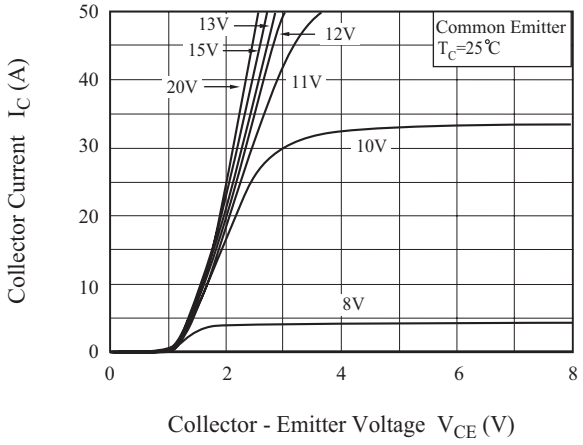


Fig 2. Saturation Voltage Characteristics

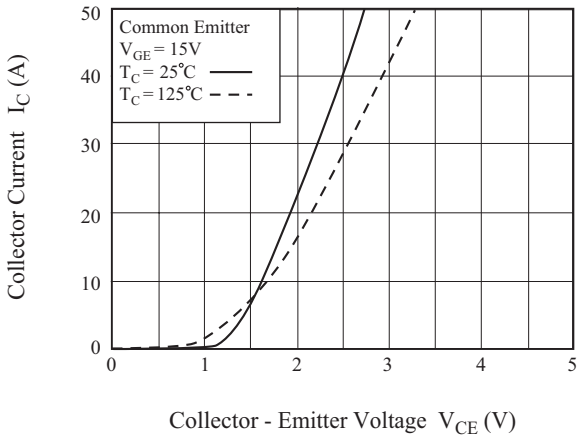


Fig 3. Saturation Voltage vs. Case Temperature

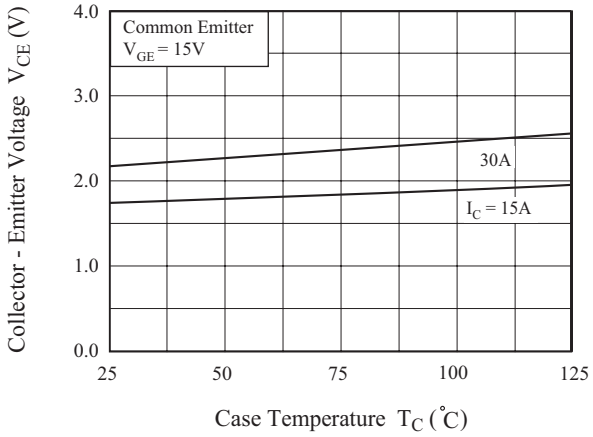


Fig 4. Saturation Voltage vs. V_{GE}

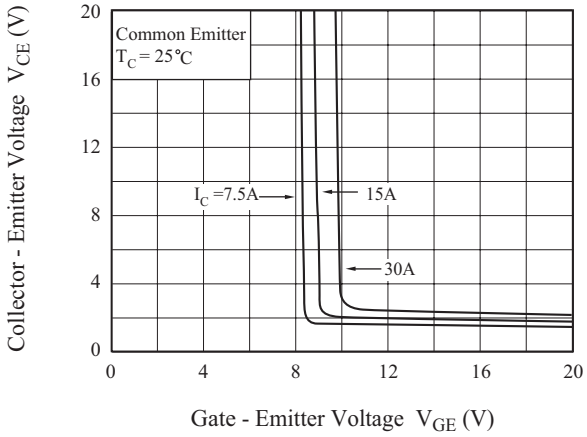


Fig 5. Saturation Voltage vs. V_{GE}

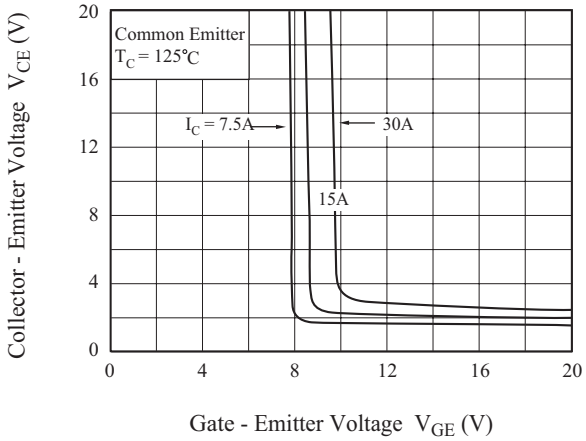


Fig 6. Capacitance Characteristics

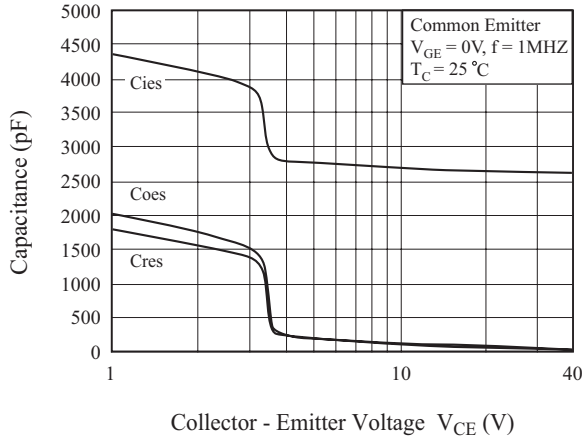


Fig 7. Turn-On Characteristics vs. Gate Resistance

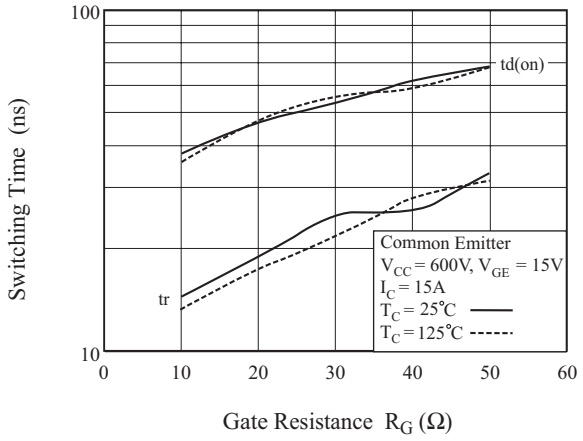


Fig 8. Turn-Off Characteristics vs. Gate Resistance

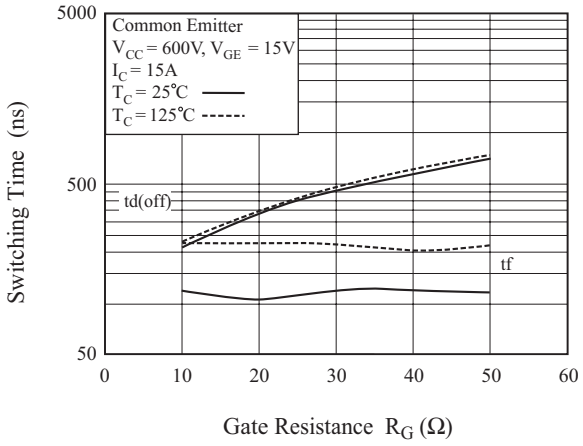


Fig 9. Switching Loss vs. Gate Resistance

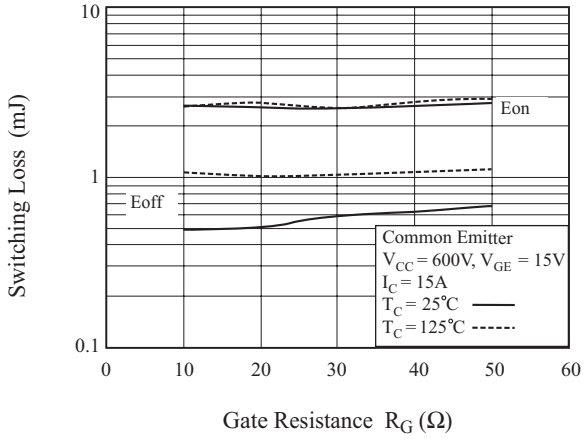


Fig 10. Turn-On Characteristics vs. Collector Current

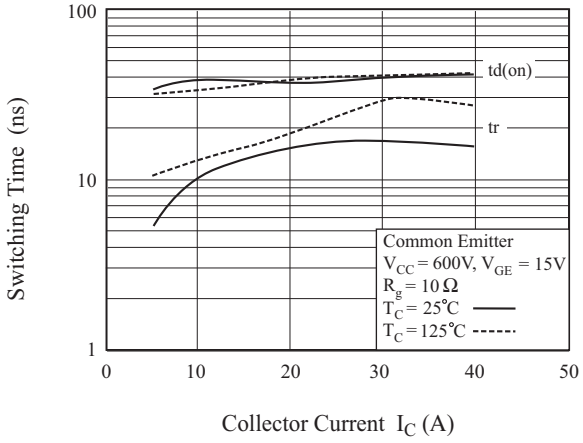


Fig 11. Turn-Off Characteristics vs. Collector Current

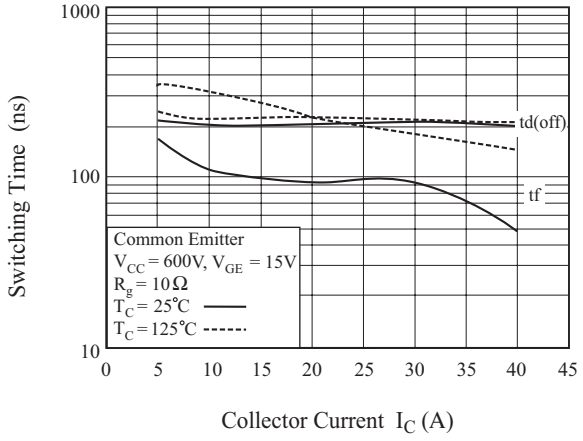


Fig 12. Switching Loss vs. Collector Current

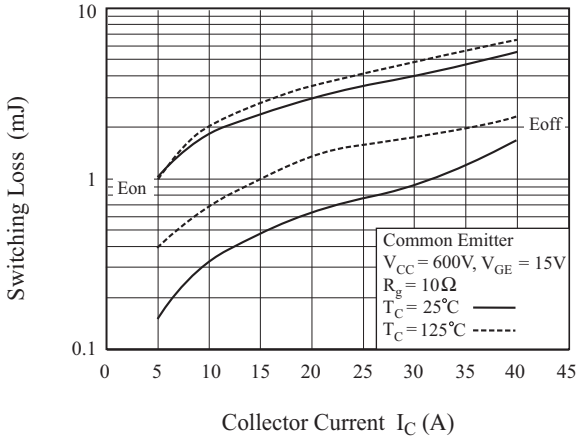


Fig 13. Gate Charge Characteristics

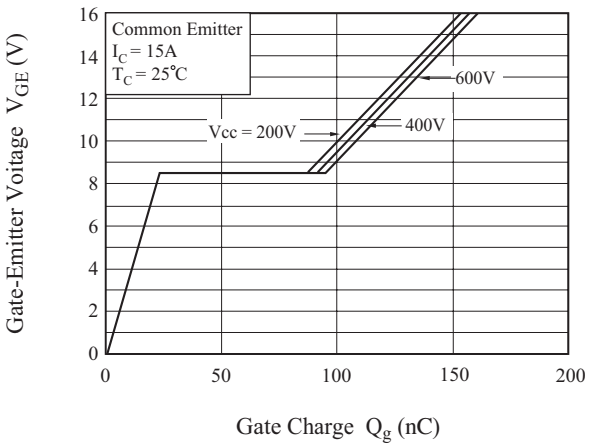


Fig 14. Forward Characteristics

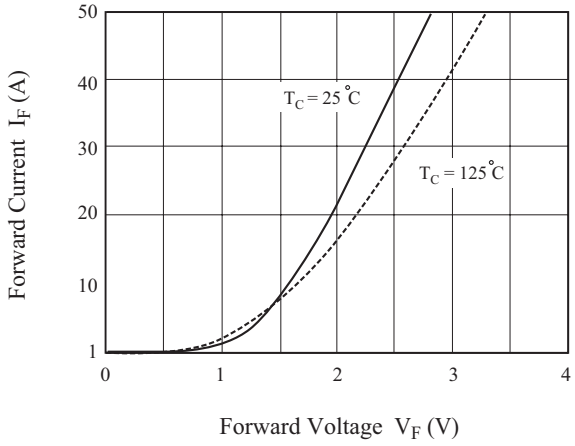


Fig 15. SOA Characteristics

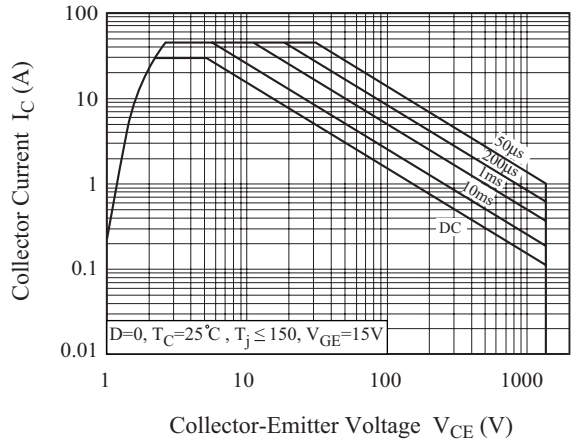


Fig 16. Transient Thermal Impedance of IGBT

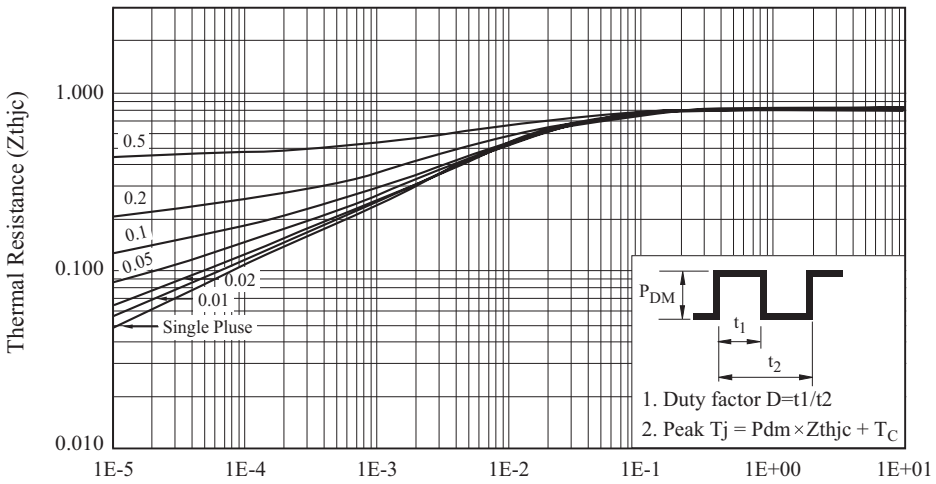


Fig 17. Switching Test Circuit

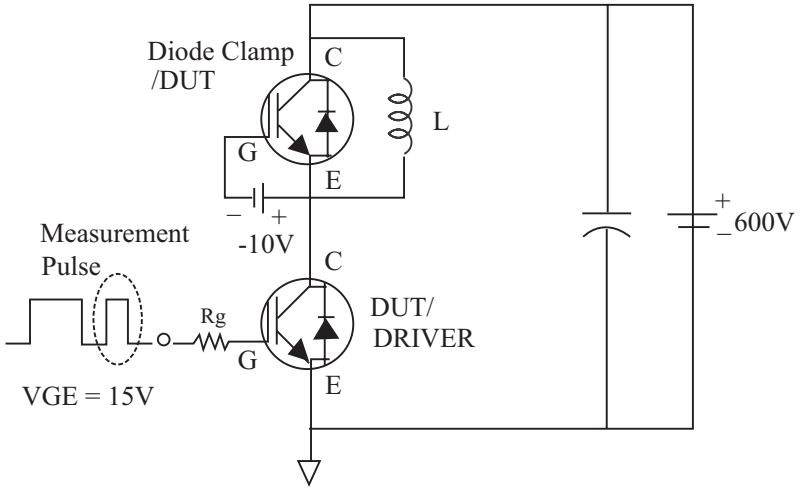


Fig 18. Definition Switching Time & Loss